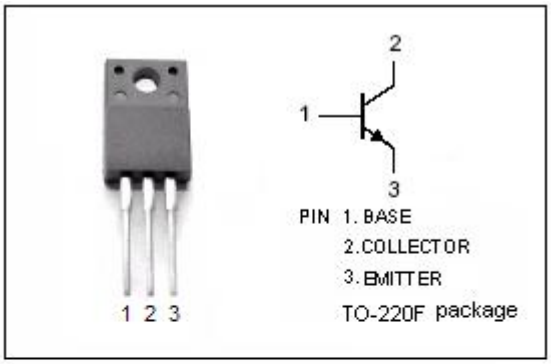
isc Silicon NPN Power Transistor — 2SC4234

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= 800V(Min)
- Fast Switching speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

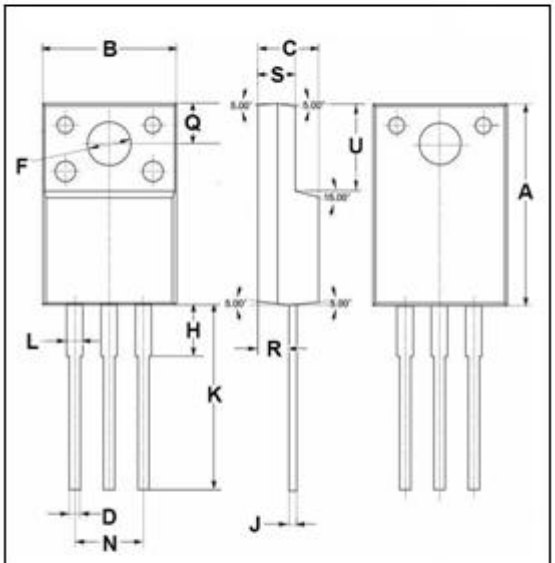
- Electronic ballasts for fluorescent lighting
- Switch mode power supplies

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1200	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	3	A
I_{CM}	Collector Current-Peak	6	A
I_B	Base Current-Continuous	1	A
I_{BM}	Base Current-Peak	2	A
P_T	Total Power Dissipation @ T_C=25℃	45	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	2.77	℃/W



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.80
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.85
U	6.40	6.60

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 0.1A; I_B= 0	800			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 1.5A; I_B= 0.3A			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 1.5A; I_B= 0.3A			1.5	V
I_{CBO}	Collector Cutoff Current	At rated Voltage			100	μA
I_{CEO}	Collector Cutoff Current	At rated Voltage			100	μA
I_{EBO}	Emitter Cutoff Current	At rated Voltage			100	μA
h_{FE-1}	DC Current Gain	I_C= 1.5A ; V_{CE}= 5V	8			
h_{FE-2}	DC Current Gain	I_C= 1mA ; V_{CE}= 5V	7			
f_T	Current-Gain—Bandwidth Product	I_C= 0.3A ; V_{CE}= 10V		8		MHz
Switching times						
t_{on}	Turn-on Time	I_C= 1.5A , I_{B1}= 0.3A; I_{B2}= -0.6A R_L= 170Ω ; V_{BB2}= 4V			0.5	μs
t_{stg}	Storage Time				3.5	μs
t_f	Fall Time				0.3	μs